

< C band internally matched power GaAs FET >

MGFC41V3642

3.6 - 4.2 GHz BAND / 14W

DESCRIPTION

The MGFC41V3642 is an internally impedance-matched GaAs power FET especially designed for use in 3.6 - 4.2 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation

Internally matched to 50(ohm) system

• High output power

P1dB=14W (TYP.) @f=3.6 - 4.2GHz

• High power gain

GLP=12.5dB (TYP.) @f=3.6 - 4.2GHz

High power added efficiency

P.A.E.=40% (TYP.) @f=3.6 - 4.2GHz

• Low distortion [item -51]

IM3=-45dBc (TYP.) @Po=30dBm S.C.L

APPLICATION

• item 01: 3.6 - 4.2 GHz band power amplifier

• item 51: 3.6 - 4.2 GHz band digital radio communication

QUALITY

• IG

RECOMMENDED BIAS CONDITIONS

• VDS=10V • ID=3.4A • RG=50ohm Refer to Bias Procedure

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit				
VGDO	Gate to drain breakdown voltage	-15	V				
VGSO	Gate to source breakdown voltage	-15	V				
ID	Drain current	12	Α				
IGR	Reverse gate current	-30	mA				
IGF	Forward gate current	63	mA				
PT *1	Total power dissipation	57.7	W				
Tch	Cannel temperature	175	°C				
Tstg	Storage temperature	-65 to +175	ç				
*1 : Tc=25°C							

OUTLINE DRAWING Unit: millimeters (inches) 24+/-0.3 R1.25 R1.2 (2) (3) 20.4+/-0.2 13.4 (1): GATE (2): SOURCE (FLANGE) (3): DRAIN

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Electrical characteristics

Symbol	Parameter	Test conditions	Limits		Unit	
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	=	12	Α
gm	Transconductance	VDS=3V,ID=3.0A	-	3	i	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=30mA	-	-	-5	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=3.4A	40	41.5	i	dBm
GLP	Linear Power Gain	f=3.6 – 4.2GHz	11	12.5	-	dB
ID	Drain current		-	3.3	ı	Α
P.A.E.	Power added efficiency		-	40	-	%
IM3 *2	3rd order IM distortion		-42	-45	-	dBc
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	-	2.8	°C/W

^{*2 :}item -51 ,2 tone test,Po=30dBm Single Carrier Level ,f=4.2GHz,delta f=10MHz

^{*3:} Channel-case

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